Silicon PNP Power Transistors 2SA483

DESCRIPTION

- With TO-66 package
- Complement to type 2SC783
- High voltage: V_{CEO}=-150V(min)

APPLICATIONS

- Power amplifier applications
- Vertical output applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Fig.1 simplified outline (TO-66) and symbol

Absolute maximum ratings(Ta=℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-150	V
V_{CEO}	Collector-emitter voltage	Open base	-150	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-1.5	A
I_E	Emitter current		1.5	A
P_C	Collector power dissipation	T_C=25℃	20	W
T_j	Junction temperature		150	℃
T_{stg}	Storage temperature		-65~150	℃

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CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=-10mA ;I_B=0	-150			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	I_C=-0.5mA ;I_E=0	-150			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=-0.5A; I_B=-50mA			-1.8	V
V_{BE}	Base-emitter on voltage	I_C=-0.5A ; V_{CE}=-10V			-1.8	V
I_{CBO}	Collector cut-off current	V_{CB}=-150V; I_E=0			-0.1	mA
I_{EBO}	Emitter cut-off current	V_{EB}=-5V; I_C=0			-0.1	mA
h_{FE}	DC current gain	I_C=-0.1A ; V_{CE}=-10V	30		240	
C_{OB}	Output capacitance	I_E=0 ; V_{CB}=-10V;f=1.0MHz		50		pF
f_T	Transition frequency	I_C=-0.1A ; V_{CE}=-10V		10		MHz

◆ **h_{FE} Classifications**

R	O	Y
30-80	70-140	120-240

PACKAGE OUTLINE

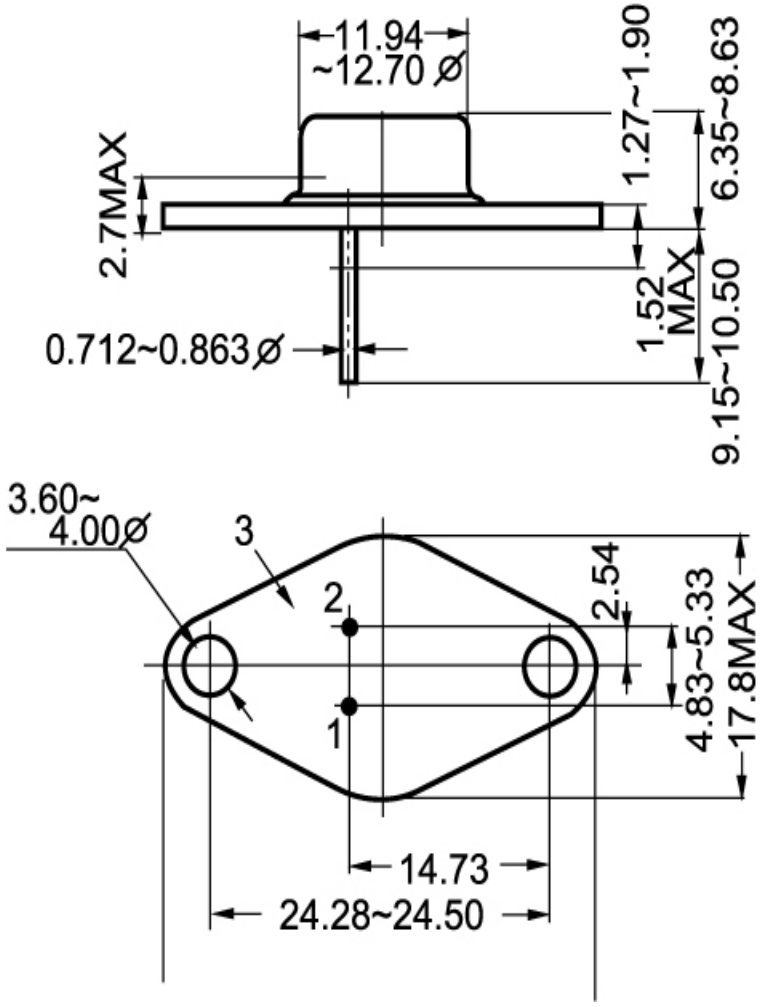

Fig.2 outline dimensions